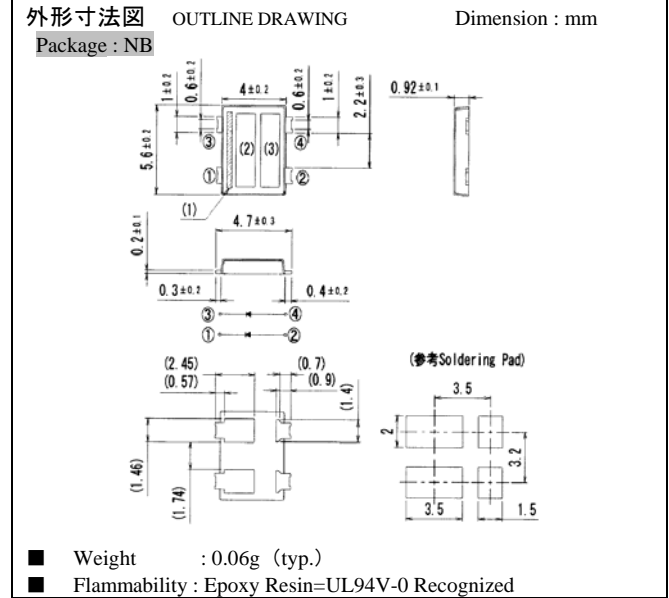


**NB10HSA08**

構造：ショットキーバリアダイオード (SBD)  
 Construction : Schottky Barrier Diode  
 用途：高周波整流用  
 Application : High-Frequency Rectification

**特長**      **Feature**  
 小型 SMD      Small SMD  
 低熱抵抗      Lower Thermal-Resistance  
 高電流      High Current Capability  
 Tj=150°C      Tj=150°C



■ 絶対最大定格 (表示無き場合 Ta=25°C) Absolute Maximum Ratings (Ta = 25 °C unless otherwise stated)

項目 Item	記号 Symbol	条件 Conditions	定格値 Rating	単位 Units	
くり返しピーク逆電圧 Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	—	80	V	
平均整流電流 Average Rectified Output Current	I <sub>O</sub>	50Hz 正弦全波通電 抵抗負荷 *1 50H Full Sine Wave, Resistive Load	Tl=91°C, VRM=40V (Tl:Lead Temperature)	10	A
			Ta=29°C *2 VRM=40V	3.0	
実効順電流 RMS Forward Current	I <sub>F(RMS)</sub>	—	11.1	A	
サージ順電流 Surge Forward Current	I <sub>FSM</sub>	50Hz 正弦全波 1 サイクル 非繰り返し 50Hz Full Sine Wave, 1 cycle, Non-repetitive	120	A	
動作接合温度範囲 Operation Junction Temperature Range	T <sub>jw</sub>	—	-40~+150	°C	
保存温度範囲 Storage Temperature Range	T <sub>stg</sub>	—	-40~+150	°C	

■ 電氣的・熱的特性 Electrical / Thermal Characteristics

項目 Item	記号 Symbol	条件 Conditions	最小値 min.	代表値 typ.	最大値 max.	単位 Units
ピーク逆電流 Peak Reverse Current	I <sub>RM</sub>	VRM=VRRM, Tj=25°C, Per diode	—	—	100	μA
ピーク順電圧 Peak Forward Voltage	V <sub>FM</sub>	IFM=5.0A, Tj=25°C, Per diode	—	—	0.7	V
接合容量 Junction Capacitance	C <sub>j</sub>	f=100kHz, VR=10V, Per diode		135	—	pF
熱抵抗 Thermal Resistance	Rth(j-l)	接合部・リード間 Junction to Lead	—	—	7	°C/W
	Rth(j-a)	接合部・周囲間 Junction to Ambient	*2 (ガラスエポキシ基板実装)	—	60	°C/W

\*1 : カソード共通動作による / Common Cathode Operation

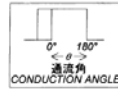
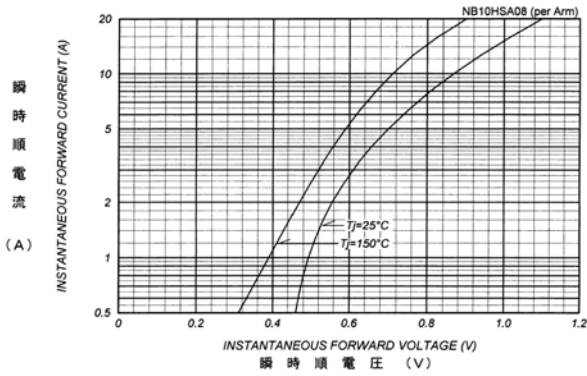
\*2 : プリント基板実装 / Glass-Epoxy Substrate Mounted (Soldering Land=2.0\*1.5mm,2.0\*3.5mm,Both Sides)

NB10HSA08

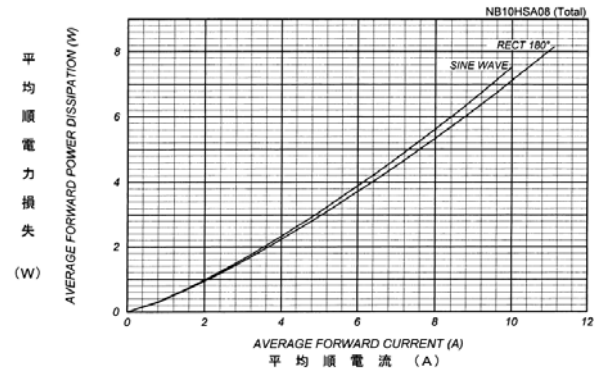
DSE-13051 (2/2)

■ 特性図 Characteristics Diagrams

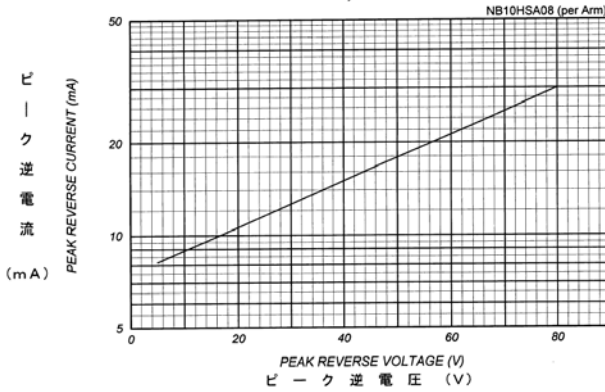
順電圧特性  
FORWARD CURRENT VS. VOLTAGE



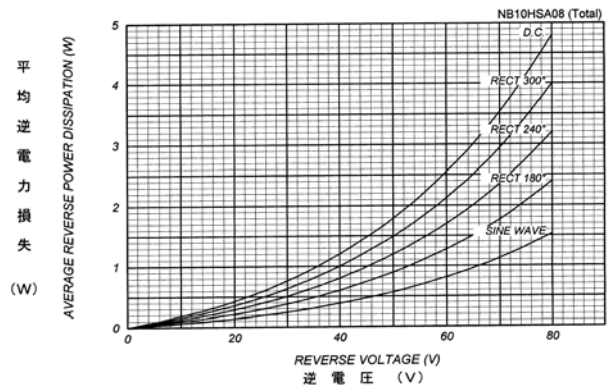
平均順電力損失特性  
AVERAGE FORWARD POWER DISSIPATION



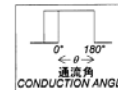
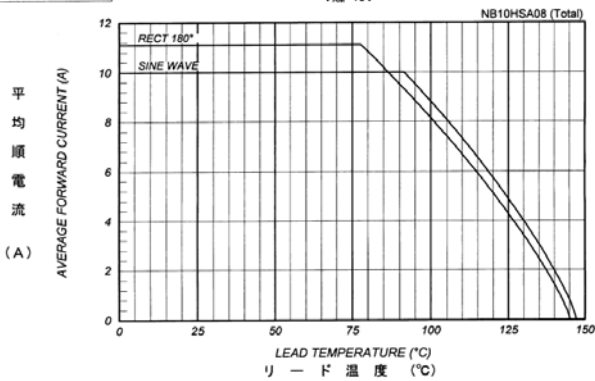
ピーク逆電流 - ピーク逆電圧特性  
PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE  
Tj = 150 °C



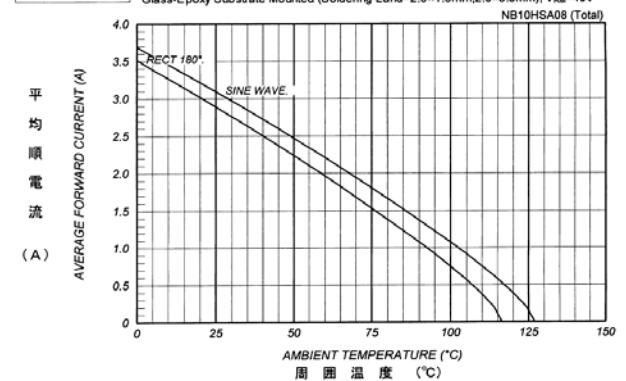
平均逆電力損失  
AVERAGE REVERSE POWER DISSIPATION



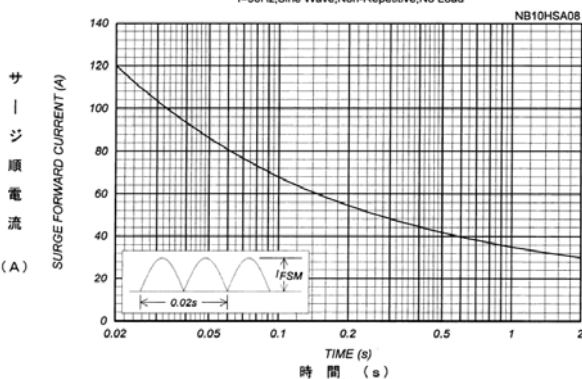
平均順電流 - リード温度定格  
AVERAGE FORWARD CURRENT VS. LEAD TEMPERATURE  
V<sub>RM</sub> = 40V



平均順電流 - 周囲温度定格  
AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE  
Glass-Epoxy Substrate Mounted (Soldering Land=2.0×1.5mm, 2.0×3.5mm), V<sub>RM</sub> = 40V



サージ順電流定格  
SURGE CURRENT RATINGS  
f = 50Hz, Sine Wave, Non-Repetitive, No Load



接合容量特性  
JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

